TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK2835

# Chopper Regulator, DC-DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & Low\ drain-source\ ON\ resistance & : R_{DS}\ (ON) = 0.56\ \Omega\ (typ.) \\ \bullet & High\ forward\ transfer\ admittance & : |Y_{fs}| = 4.5\ S\ (typ.) \\ \bullet & Low\ leakage\ current & : I_{DSS} = 100\ \mu A\ (max)\ (V_{DS} = 200\ V) \\ \bullet & Enhancement-mode & : V_{th} = 1.5 {\sim} 3.5\ V\ (V_{DS} = 10\ V,\ I_{D} = 1\ mA) \\ \end{array}$ 

#### **Maximum Ratings (Ta = 25°C)**

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	200	V	
Drain-gate voltage (Ro	<sub>SS</sub> = 20 kΩ)	$V_{DGR}$	200	V	
Gate-source voltage		$V_{GSS}$	±20	٧	
Drain current	DC (Note 1)	I <sub>D</sub>	5	Α	
	Pulse (Note 1)	I <sub>DP</sub>	20	ı	
Drain power dissipation	ı	$P_{D}$	1.3	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	65	mJ	
Avalanche current		I <sub>AR</sub>	5	Α	
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	0.13	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

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Weight: 0.54 g (typ.)

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	96.1	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:  $V_{DD}$  = 50 V,  $T_{ch}$  = 25°C (initial), L = 4.2 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 5 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.

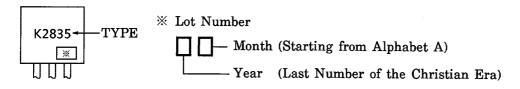
## **Electrical Characteristics (Ta = 25°C)**

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V	_	_	±10	μΑ
Drain cut-off cur	rent	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V	_	_	100	μΑ
Drain-source bro	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	200	_	_	V
Gate threshold v	oltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5	_	3.5	V
Drain-source Of	N resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A	_	0.56	0.8	Ω
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2.5 A	2.0	4.5	_	S
Input capacitanc	е	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		440	_	pF
Reverse transfer	capacitance	C <sub>rss</sub>			35	_	
Output capacitar	pacitance C <sub>oss</sub>		_	120	_		
Switching time Fal	Rise time	t <sub>r</sub>	$V_{GS}$	_	15	_	- ns
	Turn-on time	t <sub>on</sub>		_	20	_	
	Fall time	t <sub>f</sub>		_	15	_	
	Turn-off time	t <sub>off</sub>	$V_{DD} = 100V$ Duty $\leq 1\%$ , $t_{W} = 10\mu s$	_	60	_	
Total gate charg plus gate-drain)		Qg			10	_	
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$		6	_	nC
Gate-drain ("miller") Charge		Q <sub>gd</sub>			4	_	

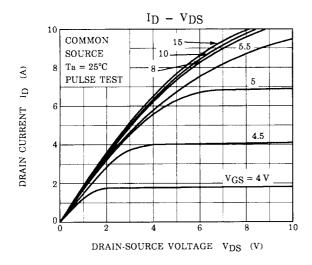
## Source-Drain Ratings and Characteristics (Ta = 25°C)

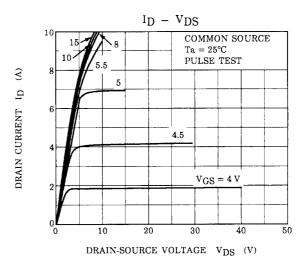
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	-	_	_	5	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	-	_	_	20	Α
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V	_	_	-2.0	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V, dI <sub>DR</sub> / dt = 100 A / μs	_	150		ns
Reverse recovery charge	Q <sub>rr</sub>		_	0.45	_	μC

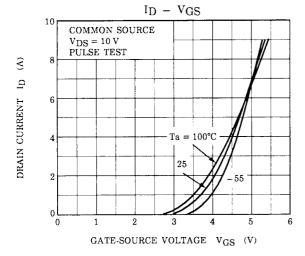
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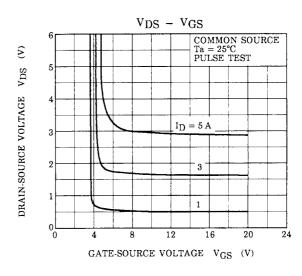


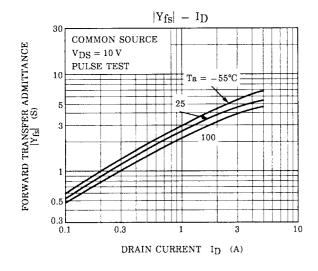
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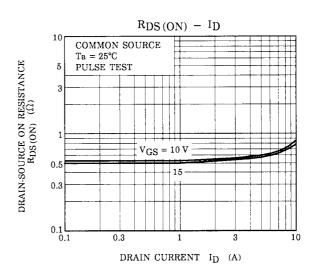




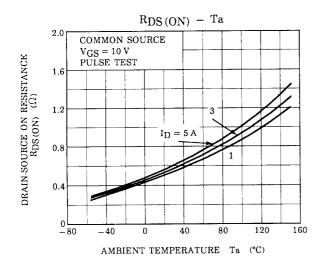


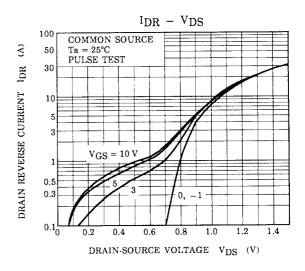


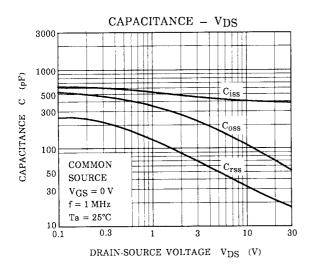


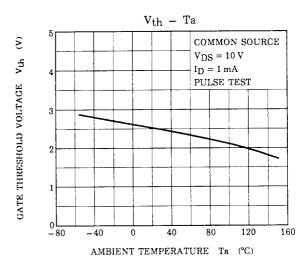


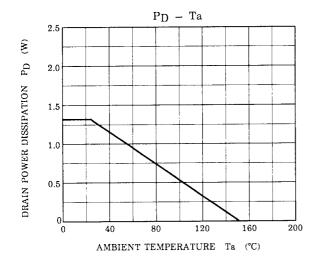
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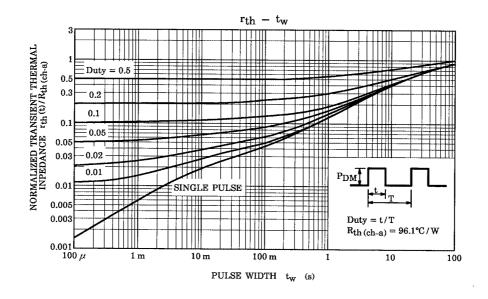


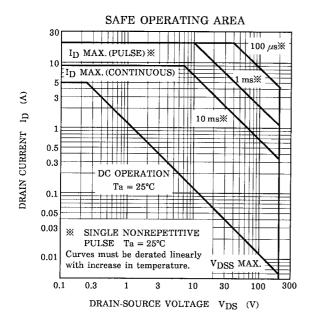


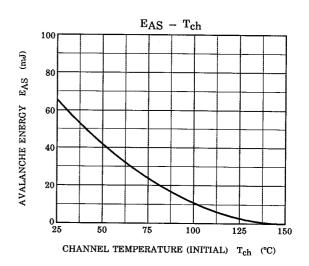


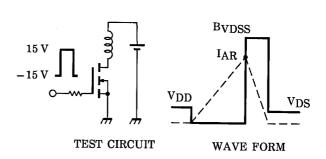


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$$R_G = 25 \Omega$$
  
 $V_{DD} = 25 V, L = 4.2 mH$ 

$$EAS = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left( \frac{BVDSS}{BVDSS - VDD} \right)$$

#### **RESTRICTIONS ON PRODUCT USE**

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